

# FISH & RICHARDSON P.C.

45 Rockefeller Plaza  
Suite 2800  
New York, New York  
10111

Telephone  
212 765-5070

Facsimile  
212 258-2291

Web Site  
www.fr.com

Date November 16, 2001

To Examiner Robert Kunemund - Art Unit 1765  
U.S. Patent Office  
Washington, DC 20231

Facsimile number 12967-00200001 / (703) 872-9439

From John B. Pegram

Re 'Tomohiro Kawase et al.  
S.N. 09/824,965  
Our Ref.: 12967-002001

Number of pages  
including this page 13

Message

NOTE: This facsimile is intended for the addressee only and may contain privileged or confidential information. If you have received this facsimile in error, please immediately call us collect at 212 765-5070 to arrange for its return. Thank you.

Attorney's Docket No.: 12967-002001

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Tomohiro Kawase et al                      Art Unit : 1765  
Serial No. : 09/824,965                                      Examiner : Robert Kunemund  
Filed : April 3, 2001  
Title : METHOD OF PREPARING GROUP III-V COMPOUND SEMICONDUCTOR  
CRYSTAL

Commissioner for Patents  
Washington, D.C. 20231

By Facsimile

PRELIMINARY AMENDMENT

Prior to examination, please amend this reissue application as follows:

In the specification:

Add the following new claims 40 - 66:

40. A method of preparing a carbon-doped group III-V compound semiconductor comprising the steps of:

melting a boron oxide substance in contact with carbon, thereby forming a boron oxide - carbon mixture,

heating and melting a III-V compound semiconductor raw material together with said boron oxide - carbon mixture.

maintaining said compound raw material in melted form for a period to permit carbon to migrate from said boron oxide - carbon mixture into said compound raw material, and

solidifying said melted compound raw material to form a crystalline carbon-doped compound semiconductor.

wherein the amount of carbon in the initial boron oxide - carbon mixture is larger than the amount of carbon doped into said compound semiconductor.

41. The method of preparing a carbon-doped group III-V compound semiconductor according to claim 40, wherein said boron oxide substance comprises boron oxide and water.